1

In The Claims

- 1. (currently amended) A wet stripping apparatus for removing unwanted film layers from a wafer surface comprising:
- a tank body for holding a volume of a stripper solution therein;
- a wafer holder for holding at least one wafer therein in a vertical position such that a planar surface of the wafer is parallel to a vertical tank wall of said tank body; and

means for reciprocally moving said wafer holder in an upand-down motion with said at least one wafer immersed in said stripper solution at a frequency of not more than up to 100 cycle/min.

- 2. (original) A wet stripping apparatus for removing unwanted film layers from a wafer surface according to claim 1 further comprising heating means in said tank body for heating said stripper solution.
- 3. (original) A wet stripping apparatus for removing unwanted film layers from a wafer surface according to claim 1, wherein said wafer holder is a front open unified pod (FOUP) for holding up to 25 wafers.

- 4. (original) A wet stripping apparatus for removing unwanted film layers from a wafer surface according to claim 1, wherein said wafer holder is a standard mechanical interface (SMIF) pod.
- 5. (original) A wet stripping apparatus for removing unwanted film layers from a wafer surface according to claim 1, wherein said means for reciprocally moving said wafer holder is an air cylinder assembly.
- 6. (original) A wet stripping apparatus for removing unwanted film layers from a wafer surface according to claim 1, wherein said means for reciprocally moving said wafer holder is an air cylinder assembly that moves at a frequency of about 60 cycle/min.
- 7. (original) A wet stripping apparatus for removing unwanted film layers from a wafer surface according to claim 2, wherein said heating means is an electrical heating means.

8. (cancelled)

9. (original) A method for removing unwanted film layers from a wafer surface by wet stripping comprising the steps of:

providing a tank body and filling the tank body with a volume of a stripper solution;

providing a wafer holder holding at least one wafer therein in a vertical position with a planar surface of the wafer parallel to a vertical tank wall of said tank body;

mounting said wafer holder in said tank body immersed in said stripper solution; and

moving said wafer holder reciprocally in an up-and-down motion with said at least one wafer immersed in said stripper solution at a frequency of not more than 100 cycle/min.

10. (currently amended) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 9 further comprising the step of filling the tank body with $\frac{1}{2}$ stripper solution that comprises dimethyl sulfoxide (DMSO).

- 11. (currently amended) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 9 further comprising the step of filling the tank body with $\frac{1}{2}$ stripper solution that comprises dimethyl sulfoxide (DMSO) and tetramethyl ammoniumhydroxide (TMAH).
- 12. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 9 further comprising the step of mounting said wafer holder in said tank body and soaking said at least one wafer in said stripper solution stationarily for at least 3 min.
- 13. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 9 further comprising the step of mounting said wafer holder in said tank body and soaking said at least one wafer in said stripper solution stationarily for at least 3 min and then moving said wafer holder up-and-down at a frequency of not more than 100 cycle/min.

14. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 9 further comprising the steps of:

rinsing said wafer holder and said at least one wafer in a quick dump rinse (QDR) process; and

spin drying said at least one wafer.

- 15. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 9 further comprising the step of moving said wafer holder reciprocally in an up-and-down motion for a length of time sufficient to remove all unwanted film layers from said wafer surface.
- 16. (original) A method for removing unwanted film layers from a wafer surface by wet stripping comprising the steps of:

providing a tank body and filling the tank body with a volume of a stripper solution;

providing a wafer holder holding at least one wafer therein in a vertical position with a planar surface of the wafer parallel to a vertical tank wall of said tank body;

mounting said wafer holder in said tank body and immersing said at least one wafer stationarily in said stripper solution for a time period of at least 3 min; and

moving said wafer holder reciprocally in an up-and-down motion with said at least one wafer immersed in said stripper solution at a frequency of not more than 100 cycle/min.

- 17. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 16 further comprising the step after said moving step of immersing said at least one wafer stationarily in said tank body for a time period of at least 10 sec.
- 18. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 16 further comprising the step of filling the tank body with a stripper solution that comprises dimethyl sulfoxide (DMSO).

19. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 16 further comprising the steps of:

rinsing said wafer holder and said at least one wafer in a quick dump rinse (QDR) process; and

spin drying said at least one wafer.

20. (original) A method for removing unwanted film layers from a wafer surface by wet stripping according to claim 16 further comprising the step of moving said wafer holder reciprocally in an up-and-down motion for a length of time sufficient to remove all unwanted film layers from said wafer surface.